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Sheet 1

of	1
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Application Number	Not Known Yet
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Filing Date	04/16/2004
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First Named Inventor	Yee-Chia Yeo
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Art Unit	Not Known Yet
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Examiner Name	Not Known Yet
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Attorney Docket Number	N1085-00180
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[illegible][illegible]

Date Considered

3/27/06

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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Complete if Known

Application Number	Not Known Yet
Filing Date	4/16/2004
First Named Inventor	Yee-Chia Yeo
Art Unit	Not Known Yet
Examiner Name	Not Yet Assigned
Attorney Docket Number	N1085-00180

Sheet 2 of 2

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
AC	I	X. Huang et al., "Sub-50 nm P-Channel FinFET", IEEE Transactions On Electron Devices, Vol. 48, No. 5, May 2001, Pages 880-886	
	J	F.-L. Yang et al., "35nm CMOS FinFETs", 2002 Symposium On VLSI Technology Digest of Technical Papers, June 2002, Pages 104-105	
	K	H.-S. P. Wong, "Beyond the conventional transistor", IBM J. Research and Development, Vol. 46, No. 2/3, March/May 2002, Pages 133-168	
	L	R. Chau et al., "Advanced Depleted-Substrate Transistors: Single-gate, Double-gate and Tri-gate" (Invited Paper), 2002 International Conference on Solid State Devices and Materials, Nagoya, Japan, September 2002, Pages 68-69	
	M	F.-L. Yang et al., "25 nm CMOS Omega FETs", International Electron Device Meeting, Dig. Technical Papers, Dec. 2002, Pages 255-258	
	N	J. P. Colinge et al., "Silicon-On-Insulator 'Gate-All-Around Device' ", International electron Device Meeting, Dig. Technical Papers, Dec. 1990, Pages 595-598	
	O	E. Leobandung et al., "Wire-channel and wrap-around-gate metal-oxide-semiconductor field-effect transistors with a significant reduction of short channel effects", J. Vacuum Science and Technology B, Vol. 15, No. 6, Nov./Dec.1997, Pages 2791-2794	
AC			

Examiner Signature		Date Considered	3/27/06
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